

# Homework #10

November 9 (to be tested on Test 3 November 17)

1. A membrane is to be manufactured to the following specifications. At 700°C the leak rate of hydrogen is not to exceed  $10^{-3} \text{ mol cm}^{-2} \text{ h}^{-1}$  when the concentrations of hydrogen are maintained at  $1.5 \times 10^{19} \text{ atoms cm}^{-3}$  on one side of the membrane and effectively zero on the other side. What is the minimum thickness of iron foil that will meet these requirements? The diffusion coefficient of atomic hydrogen in iron at 700°C is  $3.091 \times 10^{-4} \text{ cm}^2 \text{ s}^{-1}$ .
2. To increase its corrosion resistance, chromium is diffused into steel at 980°C. If during diffusion the surface concentration of chromium remains constant at 100%, how long will it take (in days) to achieve a Cr concentration of 1.8% at a depth of 0.002 cm below the steel surface? ( $D_0 = 0.54 \text{ cm}^2/\text{s}$ ;  $E_a = 286 \text{ kJ/mol}$ )
3. By planar diffusion of antimony (Sb) into *p*-type germanium, a *p-n* junction is obtained at a depth of  $3 \times 10^{-3} \text{ cm}$  below the surface. What is the donor concentration in the bulk germanium if diffusion is carried out for three hours at 790°C? The surface concentration of antimony is held constant at a value of  $8 \times 10^{18} \text{ cm}^{-3}$ ;  $D_{790^\circ\text{C}} = 4.8 \times 10^{-11} \text{ cm}^2 \text{ s}^{-1}$ .
4. You wish to dope a single crystal of silicon with boron. The specification reads  $5 \times 10^{16}$  boron atoms  $\text{cm}^{-3}$  at a depth of 25  $\mu\text{m}$  from the surface of the silicon. What must be the effective concentration of boron in units of atoms  $\text{cm}^{-3}$  if you are to meet specification within a time of 90 minutes? Assume that initially the concentration of boron in the silicon crystal is zero. The diffusion coefficient of boron in silicon has a value of  $7.23 \times 10^{-9} \text{ cm}^2 \text{ s}^{-1}$  at the processing temperature.
5. A slab of plate glass containing dissolved helium is placed in a vacuum furnace at a temperature of 400°C to remove the helium from the glass. Before vacuum treatment, the concentration of helium is constant throughout the glass. After 10 minutes in vacuum at 400°C, at what depth from the surface of the glass has the concentration of helium decreased to  $\frac{1}{3}$  of its initial value? The diffusion coefficient of helium in the plate glass at the processing temperature has a value of  $3.091 \times 10^{-6} \text{ cm}^2 \text{ s}^{-1}$ .